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Kind regards,

Team Nexperia



# PMBTA45

500 V, 150 mA NPN high-voltage low  $V_{CEsat}$  (BISS) transistor

Rev. 02 — 10 March 2010

Product data sheet

## 1. Product profile

### 1.1 General description

NPN high-voltage low  $V_{CEsat}$  Breakthrough In Small Signal (BISS) transistor in a SOT23 (TO-236AB) small Surface-Mounted Device (SMD) plastic package.

PNP complement: PBHV9050T.

### 1.2 Features and benefits

- High voltage
- Low collector-emitter saturation voltage  $V_{CEsat}$
- High collector current capability  $I_C$  and  $I_{CM}$
- High collector current gain ( $h_{FE}$ ) at high  $I_C$
- AEC-Q101 qualified

### 1.3 Applications

- Electronic ballasts
- LED driver for LED chain module
- LCD backlighting
- Automotive motor management
- Flyback converters
- Hook switch for wired telecom
- Switch Mode Power Supply (SMPS)

### 1.4 Quick reference data

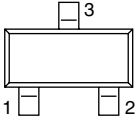
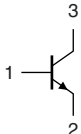
Table 1. Quick reference data

| Symbol     | Parameter                      | Conditions                                 | Min | Typ | Max  | Unit |
|------------|--------------------------------|--|-----|-----|------|------|
| $V_{CESM}$ | collector-emitter peak voltage | $V_{BE} = 0\text{ V}$                      | -   | -   | 500  | V    |
| $V_{CEO}$  | collector-emitter voltage      | open base                                  | -   | -   | 500  | V    |
| $I_C$      | collector current              |  | -   | -   | 0.15 | A    |
| $h_{FE}$   | DC current gain                | $V_{CE} = 10\text{ V}; I_C = 30\text{ mA}$ | 50  | 100 | -    |      |



## 2. Pinning information

Table 2. Pinning

| Pin | Description | Simplified outline  | Graphic symbol  |
|-----|-------------|---|---|
| 1   | base        |  |  |
| 2   | emitter     |   |   |
| 3   | collector   |   |   |

*sym021*

## 3. Ordering information

Table 3. Ordering information

| Type number | Package |  |         |
|-------------|---------|--|---------|
|             | Name    | Description                              | Version |
| PMBTA45     | -       | plastic surface-mounted package; 3 leads | SOT23   |

## 4. Marking

Table 4. Marking codes

| Type number | Marking code <sup>[1]</sup> |
|-------------|-----------------------------|
| PMBTA45     | LK*                         |

- [1] \* = -: made in Hong Kong  
 \* = p: made in Hong Kong  
 \* = t: made in Malaysia  
 \* = W: made in China

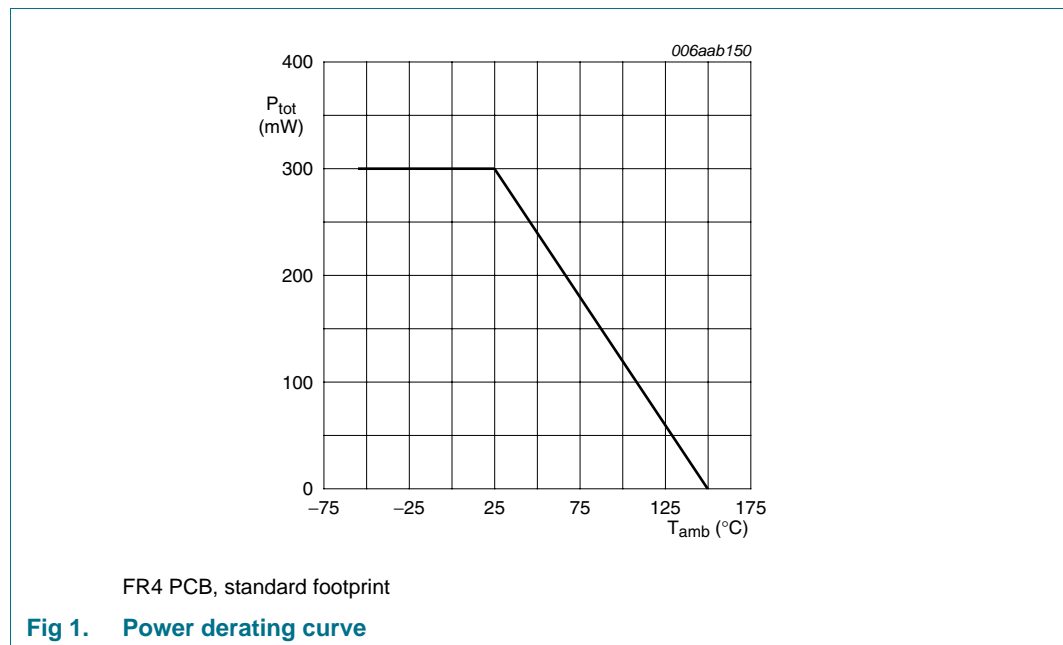
## 5. Limiting values

**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol     | Parameter                      | Conditions                       | Min | Max  | Unit |
|------------|--------------------------------|----------------------------------|-----|------|------|
| $V_{CBO}$  | collector-base voltage         | open emitter                     | -   | 500  | V    |
| $V_{CEO}$  | collector-emitter voltage      | open base                        | -   | 500  | V    |
| $V_{CESM}$ | collector-emitter peak voltage | $V_{BE} = 0$ V                   | -   | 500  | V    |
| $V_{EBO}$  | emitter-base voltage           | open collector                   | -   | 6    | V    |
| $I_C$      | collector current              |                                  | -   | 0.15 | A    |
| $I_{CM}$   | peak collector current         | single pulse;<br>$t_p \leq 1$ ms | -   | 0.5  | A    |
| $I_{BM}$   | peak base current              | single pulse;<br>$t_p \leq 1$ ms | -   | 200  | mA   |
| $P_{tot}$  | total power dissipation        | $T_{amb} \leq 25$ °C             | [1] | 300  | mW   |
| $T_j$      | junction temperature           |                                  | -   | 150  | °C   |
| $T_{amb}$  | ambient temperature            |                                  | -55 | +150 | °C   |
| $T_{stg}$  | storage temperature            |                                  | -65 | +150 | °C   |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

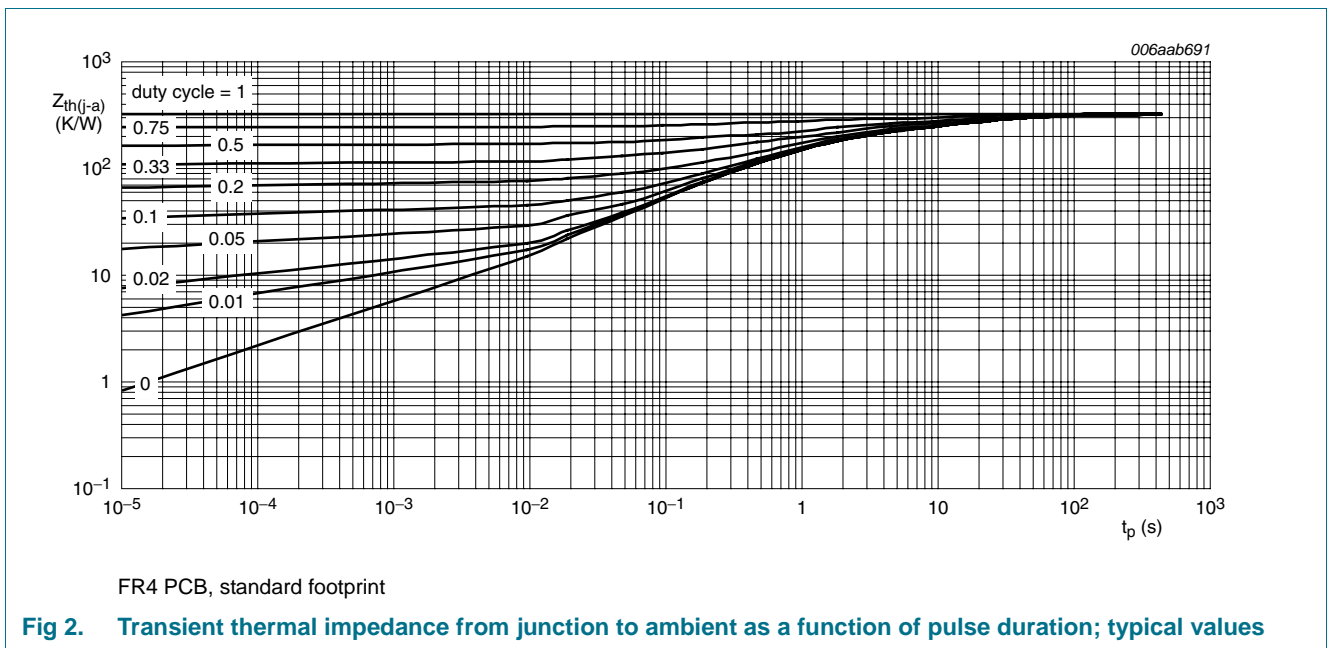


## 6. Thermal characteristics

**Table 6. Thermal characteristics**

| Symbol         | Parameter  | Conditions  | Min | Typ | Max | Unit |
|----------------|--|-------------|-----|-----|-----|------|
| $R_{th(j-a)}$  | thermal resistance from junction to ambient      | in free air | [1] | -   | 417 | K/W  |
| $R_{th(j-sp)}$ | thermal resistance from junction to solder point |             | -   | -   | 70  | K/W  |

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



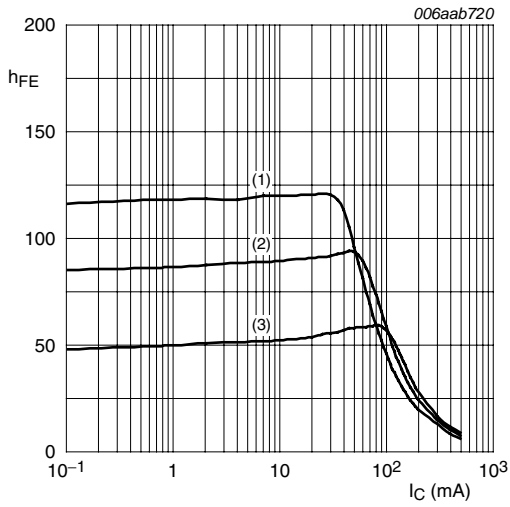
## 7. Characteristics

**Table 7. Characteristics**

$T_{amb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified.

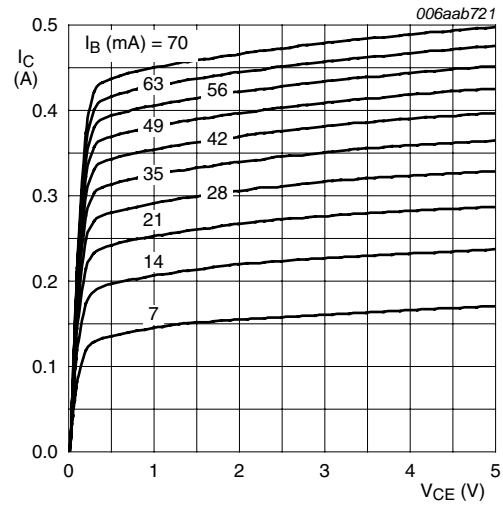
| Symbol      | Parameter                            | Conditions   | Min    | Typ  | Max | Unit          |
|-------------|--------------------------------------|--|--------|------|-----|---------------|
| $I_{CBO}$   | collector-base cut-off current       | $V_{CB} = 360\text{ V}; I_E = 0\text{ A}$  | -      | -    | 100 | nA            |
|             |                                      | $V_{CB} = 360\text{ V}; I_E = 0\text{ A}; T_j = 150\text{ }^{\circ}\text{C}$                 | -      | -    | 10  | $\mu\text{A}$ |
| $I_{CES}$   | collector-emitter cut-off current    | $V_{CE} = 360\text{ V}; V_{BE} = 0\text{ V}$   | -      | -    | 100 | nA            |
| $I_{EBO}$   | emitter-base cut-off current         | $V_{EB} = 5\text{ V}; I_C = 0\text{ A}$  | -      | -    | 100 | nA            |
| $h_{FE}$    | DC current gain                      | $V_{CE} = 10\text{ V}$   |        |      |     |               |
|             |                                      | $I_C = 30\text{ mA}$   | 50     | 100  | -   |               |
|             |                                      | $I_C = 50\text{ mA}$   | [1] 50 | 100  | -   |               |
| $V_{CEsat}$ | collector-emitter saturation voltage | $I_C = 20\text{ mA}; I_B = 2\text{ mA}$  | -      | 60   | 75  | mV            |
|             |                                      | $I_C = 50\text{ mA}; I_B = 6\text{ mA}$  | [1] -  | 65   | 90  | mV            |
| $V_{BEsat}$ | base-emitter saturation voltage      | $I_C = 50\text{ mA}; I_B = 5\text{ mA}$  | [1] -  | 0.75 | 0.9 | V             |
| $f_T$       | transition frequency                 | $V_{CE} = 10\text{ V}; I_E = 10\text{ mA}; f = 100\text{ MHz}$                               | -      | 35   | -   | MHz           |
| $C_c$       | collector capacitance                | $V_{CB} = 20\text{ V}; I_E = I_E = 0\text{ A}; f = 1\text{ MHz}$                             | -      | 4    | -   | pF            |
| $C_e$       | emitter capacitance                  | $V_{EB} = 0.5\text{ V}; I_C = I_C = 0\text{ A}; f = 1\text{ MHz}$                            | -      | 200  | -   | pF            |
| $t_d$       | delay time                           | $V_{CC} = 20\text{ V}; I_C = 0.05\text{ A}; I_{Bon} = 5\text{ mA}; I_{Boff} = -10\text{ mA}$ | -      | 80   | -   | ns            |
| $t_r$       | rise time                            |  | -      | 2700 | -   | ns            |
| $t_{on}$    | turn-on time                         |  | -      | 2780 | -   | ns            |
| $t_s$       | storage time                         |  | -      | 3400 | -   | ns            |
| $t_f$       | fall time                            |  | -      | 800  | -   | ns            |
| $t_{off}$   | turn-off time                        |  | -      | 4200 | -   | ns            |

[1] Pulse test:  $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02$ .



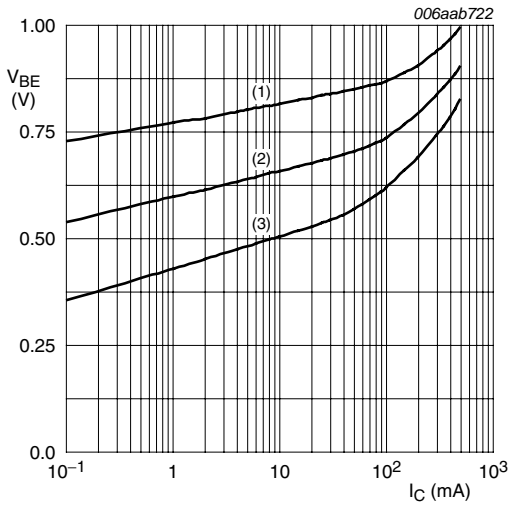
$V_{CE} = 10\text{ V}$   
 (1)  $T_{amb} = 100\text{ }^\circ\text{C}$   
 (2)  $T_{amb} = 25\text{ }^\circ\text{C}$   
 (3)  $T_{amb} = -55\text{ }^\circ\text{C}$

**Fig. 3. DC current gain as a function of collector current; typical values**



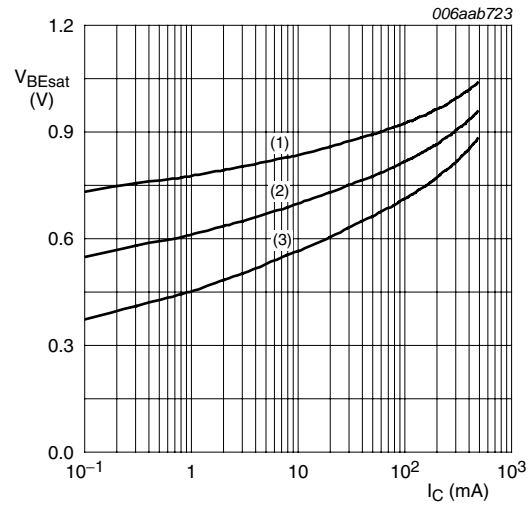
$T_{amb} = 25\text{ }^\circ\text{C}$

**Fig. 4. Collector current as a function of collector-emitter voltage; typical values**



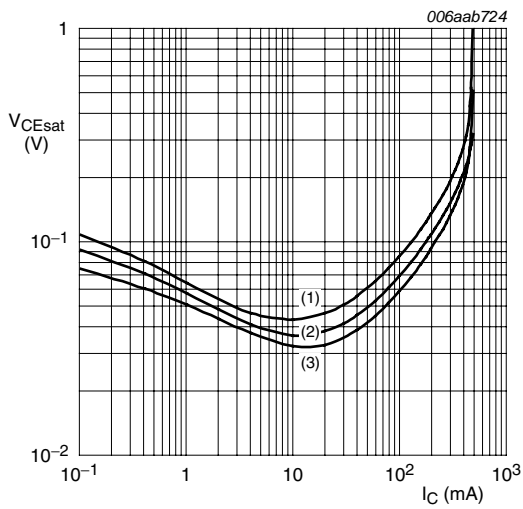
$V_{CE} = 10\text{ V}$   
 (1)  $T_{amb} = -55\text{ }^\circ\text{C}$   
 (2)  $T_{amb} = 25\text{ }^\circ\text{C}$   
 (3)  $T_{amb} = 100\text{ }^\circ\text{C}$

**Fig. 5. Base-emitter voltage as a function of collector current; typical values**



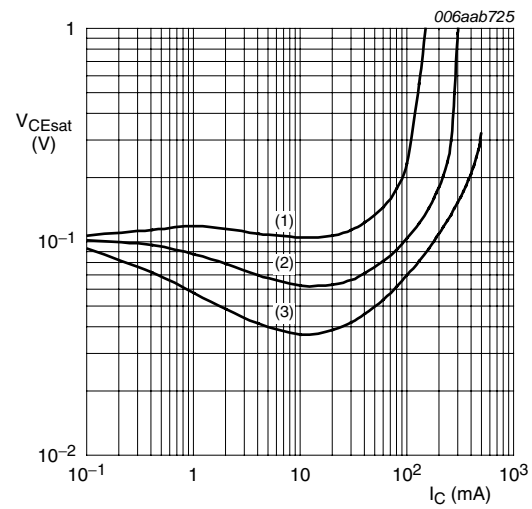
$I_C/I_B = 5$   
 (1)  $T_{amb} = -55\text{ }^\circ\text{C}$   
 (2)  $T_{amb} = 25\text{ }^\circ\text{C}$   
 (3)  $T_{amb} = 100\text{ }^\circ\text{C}$

**Fig. 6. Base-emitter saturation voltage as a function of collector current; typical values**



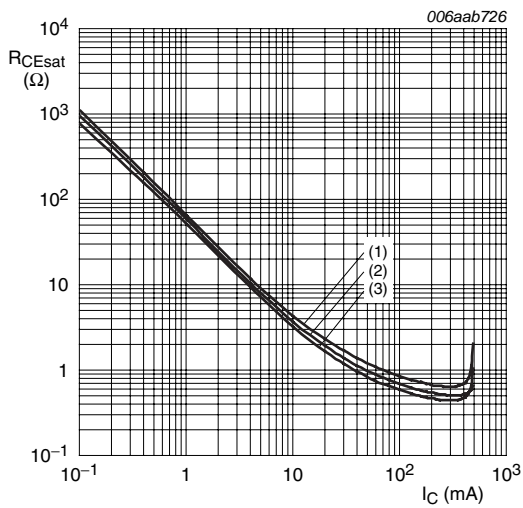
- $I_C/I_B = 5$
- (1)  $T_{amb} = 100\text{ °C}$
  - (2)  $T_{amb} = 25\text{ °C}$
  - (3)  $T_{amb} = -55\text{ °C}$

**Fig 7. Collector-emitter saturation voltage as a function of collector current; typical values**



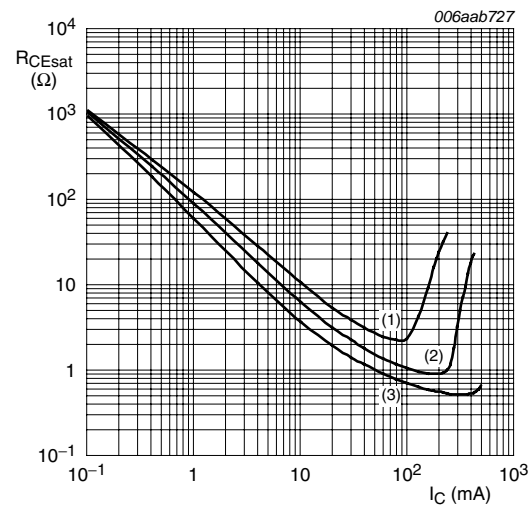
- $T_{amb} = 25\text{ °C}$
- (1)  $I_C/I_B = 20$
  - (2)  $I_C/I_B = 10$
  - (3)  $I_C/I_B = 5$

**Fig 8. Collector-emitter saturation voltage as a function of collector current; typical values**



- $I_C/I_B = 5$
- (1)  $T_{amb} = 100\text{ °C}$
  - (2)  $T_{amb} = 25\text{ °C}$
  - (3)  $T_{amb} = -55\text{ °C}$

**Fig 9. Collector-emitter saturation resistance as a function of collector current; typical values**

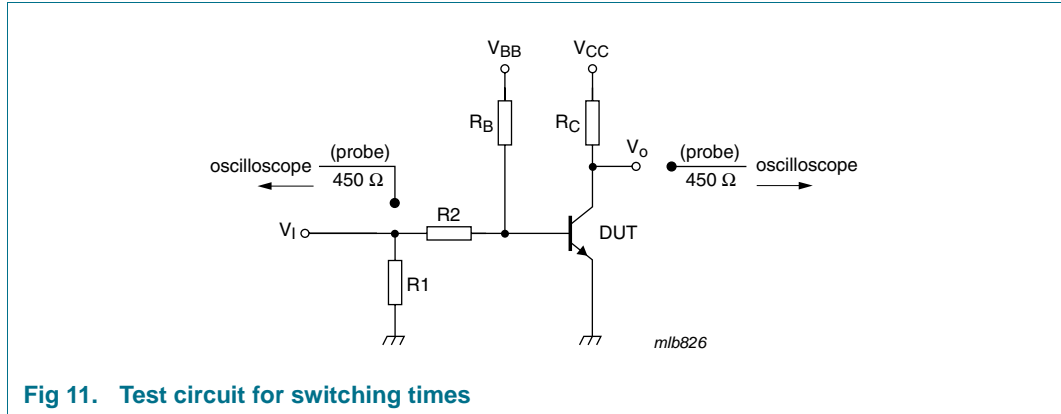


- $T_{amb} = 25\text{ °C}$
- (1)  $I_C/I_B = 20$
  - (2)  $I_C/I_B = 10$
  - (3)  $I_C/I_B = 5$

**Fig 10. Collector-emitter saturation resistance as a function of collector current; typical values**



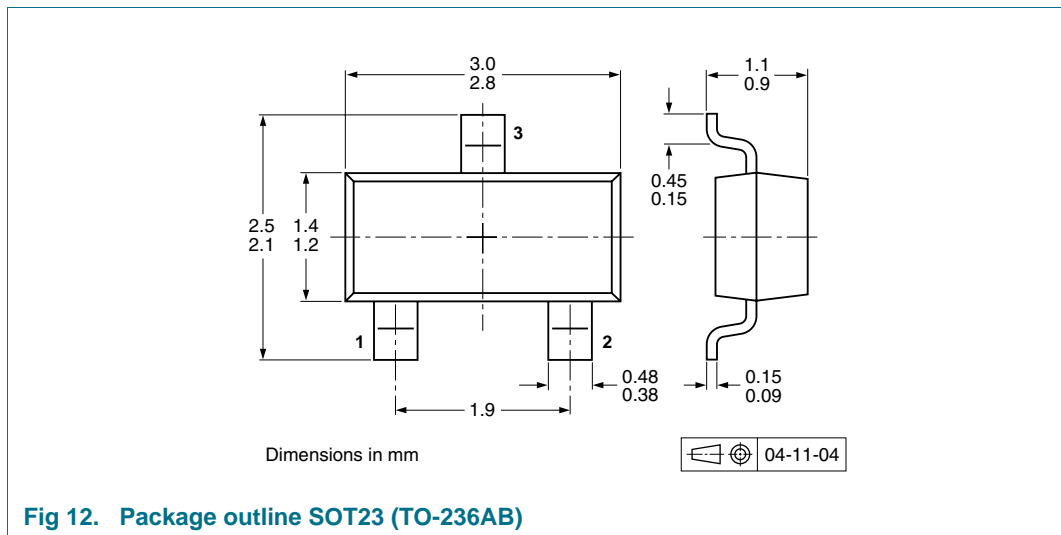
## 8. Test information



### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

## 9. Package outline



## 10. Packing information

**Table 8. Packing methods**

The indicated -xxx are the last three digits of the 12NC ordering code.<sup>[1]</sup>

| Type number | Package | Description                    | Packing quantity |       |
|-------------|---------|--------------------------------|------------------|-------|
|             |         |                                | 3000             | 10000 |
| PMBTA45     | SOT23   | 4 mm pitch, 8 mm tape and reel | -215             | -235  |

[1] For further information and the availability of packing methods, see [Section 14](#).

### 11. Soldering

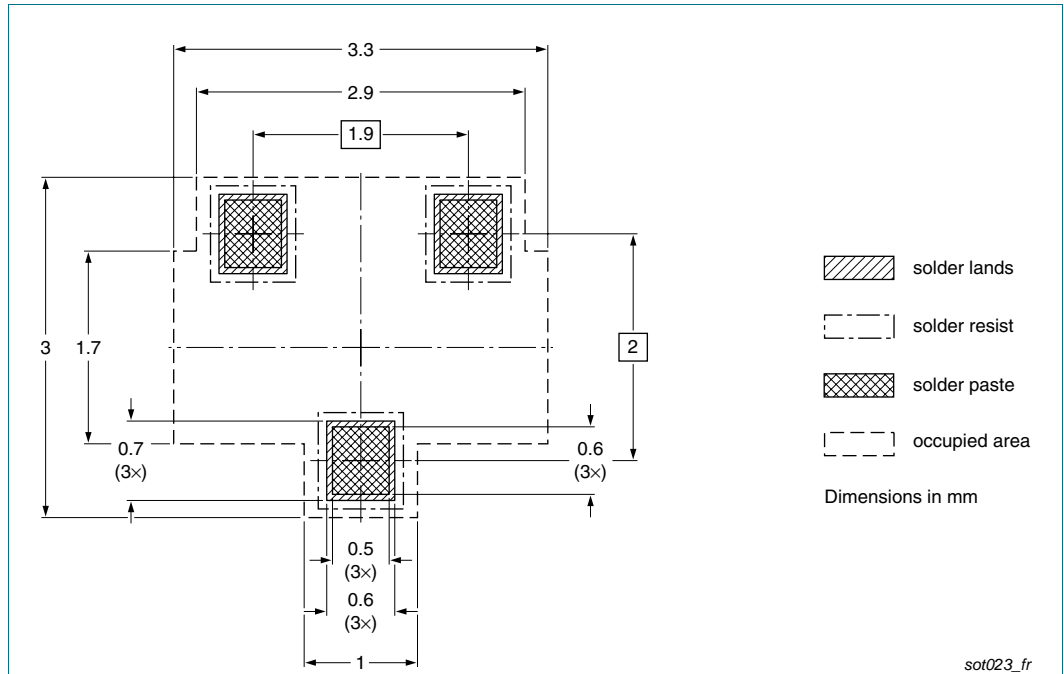


Fig 13. Reflow soldering footprint SOT23 (TO-236AB)

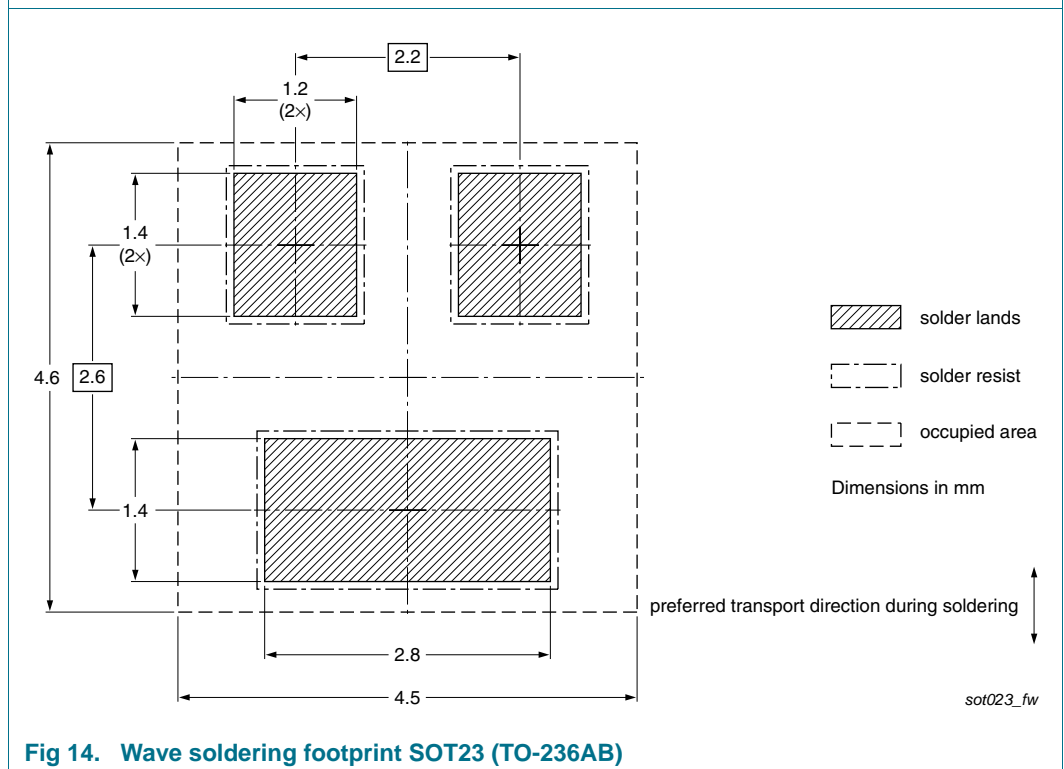


Fig 14. Wave soldering footprint SOT23 (TO-236AB)

## 12. Revision history

Table 9. Revision history

| Document ID    | Release date                         | Data sheet status  | Change notice | Supersedes |
|----------------|--------------------------------------|--------------------|---------------|------------|
| PMBTA45_2      | 20100310                             | Product data sheet | -             | PMBTA45_1  |
| Modifications: | • <a href="#">Figure 7</a> : updated |                    |               |            |
| PMBTA45_1      | 20090916                             | Product data sheet | -             | -          |

## 13. Legal information

### 13.1 Data sheet status

| Document status <sup>[1][2]</sup> | Product status <sup>[3]</sup> | Definition  |
|-----------------------------------|-------------------------------|---|
| Objective [short] data sheet      | Development                   | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet    | Qualification                 | This document contains data from the preliminary specification.                       |
| Product [short] data sheet        | Production                    | This document contains the product specification.                                     |

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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